What is claimed is:

1. An electro-optical device wherein an EL element is in contact with an insulating film including at least one of the elements selected from a group consisting of B (boron), C (carbon), N (nitrogen) and at least one of the elements selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus).

2. An electro-optical device wherein an EL element is in contact with an insulating film comprising one selected from a group consisting of aluminum nitride, silicon carbide, silicon nitride, boron nitride, boron phosphate and aluminum oxide.

3. An electro-optical device wherein an EL element is in contact with an insulating film comprising Si, Al, N, O and M where M is a rare earth element, preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), (La) lanthanum, Gd (gadolinium), Dy (dysprosium) and Nd (neodymium).

4. An electro-optical device wherein an EL element is in contact with a carbon film.

5. An electro-optical device according to claim 4 wherein the carbon film is a diamond film or a diamond-like-carbon film.

6. An electro-optical device in which an EL element is enclosed by insulating films that comprise an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon)

and P (phosphorus).

7. An electro-optical device wherein an EL element is enclosed by insulating films that comprise one selected from a group consisting of aluminum nitride, silicon carbide, silicon nitride, boron nitride, boron phosphate and aluminum oxide.

8. An electro-optical device wherein an EL element is enclosed by insulating films that comprise Si, Al, N, O and M where M is a rare earth element, preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), (La) lanthanum, Gd (gadolinium), Dy (dysprosium) and Nd (neodymium).

9. An electro-optical device wherein an EL element is enclosed by carbon films.

10. An electro-optical device according to claim 9 wherein the carbon films are a diamond film or a diamond-like-carbon film.

11. A device according to claim 1 wherein the EL element is electrically connected to a second TFT which has a gate electrically connected to a first TFT.

12. A device according to claim 2 wherein the EL element is electrically connected to a second TFT which has a gate electrically connected to a first TFT.

13. A device according to claim 3 wherein the EL element is

electrically connected to a second TFT which has a gate electrically connected to a first TFT.

14. A device according to claim 4 wherein the EL element is electrically connected to a second TFT which has a gate electrically connected to a first TFT.

15. A device according to claim 5 wherein the EL element is electrically connected to a second TFT which has a gate electrically connected to a first TFT.

16. A device according to claim 6 wherein the EL element is electrically connected to a second TFT which has a gate electrically connected to a first TFT.

17. A device according to claim 7 wherein the EL element is electrically connected to a second TFT which has a gate electrically connected to a first TFT.

18. A device according to claim 8 wherein the EL element is electrically connected to a second TFT which has a gate electrically connected to a first TFT.

19. A device according to claim 9 wherein the EL element is electrically connected to a second TFT which has a gate electrically connected to a first TFT.

20. A device according to claim 11 wherein the first TFT is a switching

element and the second TFT is a current controlling element.

21. A device according to claim 12 wherein the first TFT is a switching element and the second TFT is a current controlling element.

22. A device according to claim 13 wherein the first TFT is a switching element and the second TFT is a current controlling element.

23. A device according to claim 14 wherein the first TFT is a switching element and the second TFT is a current controlling element.

24. A device according to claim 15 wherein the first TFT is a switching element and the second TFT is a current controlling element.

25. A device according to claim 16 wherein the first TFT is a switching element and the second TFT is a current controlling element.

26. A device according to claim 17 wherein the first TFT is a switching element and the second TFT is a current controlling element.

27. A device according to claim 18 wherein the first TFT is a switching element and the second TFT is a current controlling element.

28. A device according to claim 19 wherein the first TFT is a switching element and the second TFT is a current controlling element.

29. A device according to claim 1 wherein the insulating film is disposed in a laminate with silicon oxide film, silicon nitride film or a silicon oxynitride film.

30. A device according to claim 2 wherein the insulating film is disposed in a laminate with silicon oxide film, silicon nitride film or a silicon oxynitride film.

31. A device according to claim 3 wherein the insulating film is disposed in a laminate with silicon oxide film, silicon nitride film or a silicon oxynitride film.

32. A device according to claim 4 wherein the insulating film is disposed in a laminate with silicon oxide film, silicon nitride film or a silicon oxynitride film.

33.A device according to claim 5 wherein the insulating film is disposed in a laminate with silicon oxide film, silicon nitride film or a silicon oxynitride film.

34.A device according to claim 6 wherein the insulating film is disposed in a laminate with silicon oxide film, silicon nitride film or a silicon oxynitride film.

35.A device according to claim 7 wherein the insulating film is disposed in a laminate with silicon oxide film, silicon nitride film or a silicon oxynitride film.

36.A device according to claim 8 wherein the insulating film is disposed in a laminate with silicon oxide film, silicon nitride film or a silicon oxynitride film.

37.A device according to claim 9 wherein the insulating film is disposed in a laminate with silicon oxide film, silicon nitride film or a silicon oxynitride film.

38. A device according to claim 1 wherein the EL element is formed over a resin film and an insulating film is disposed between the resin film and the EL element.

39. A device according to claim 2 wherein the EL element is formed over a resin film and an insulating film is disposed between the resin film and the EL element.

40. A device according to claim 3 wherein the EL element is formed over a resin film and an insulating film is disposed between the resin film and the EL element.

41. A device according to claim 4 wherein the EL element is formed over a resin film and an insulating film is disposed between the resin film and the EL element.

42. A device according to claim 5 wherein the EL element is formed over a resin film and an insulating film is disposed between the resin film and the EL element.

43. A device according to claim 6 wherein the EL element is formed over a resin film and an insulating film is disposed between the resin film and the EL element.

44. A device according to claim 7 wherein the EL element is formed over a resin film and an insulating film is disposed between the resin film and the EL element.

45. A device according to claim 8 wherein the EL element is formed over a resin film and an insulating film is disposed between the resin film and the EL element.

46. A device according to claim 9 wherein the EL element is formed over a resin film and an insulating film is disposed between the resin film and the EL element.

47. An electronic device which comprises an electro-optical device according to claim 1.

48. A device according to claim 11 wherein the first TFT and the second TFT are disposed on an insulating film, wherein the insulating film is an insulating film that comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus), or an insulating film that comprises Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), (La) lanthanum, Gd (gadolinium), Dy (dysprosium) and Nd (neodymium).

49. A method for manufacturing an electro-optical device comprising the steps of:

forming a plurality of TFTs over a substrate;

forming an insulating film that cover the plurality of TFTs;

forming a passivation film over the insulating film; and

forming an EL element over the passivation film.

50. A method according to claim 49 wherein the insulating film comprises a resin film.

51. A method according to claim 49 wherein the passivation film comprises an insulating film that comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus), or an insulating film that comprises Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), (La) lanthanum, Gd (gadolinium), Dy (dysprosium) and Nd (neodymium).

52. A method for manufacturing an electro-optical device comprising the steps of:

forming a plurality of TFTs over a substrate;

forming an insulating film that covers the plurality of TFTs;

forming a first passivation film over the insulating film;

forming an EL element over the first passivation film; and

forming a second passivation film that covers the EL element,

wherein the EL element is enclosed by the first passivation film and the second passivation film.

53. A method according to claim 52 wherein the insulating film comprises a resin film.

54. A method according to claim 52 wherein the first passivation film and the second passivation film comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus).

55. A method according to claim 52 wherein the first passivation film and the second passivation film comprises Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), (La) lanthanum, Gd (gadolinium), Dy (dysprosium) and Nd (neodymium).

56. A method according to claim 49 further comprising a step of forming an insulating film that comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus), between the substrate and the plurality of TFTs.

57. A method according to claim 52 further comprising a step of forming an insulating film that comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting

of Al (aluminum), Si (silicon) and P (phosphorus), between the substrate and the plurality of TFTs.

58. A method according to claim 49 further comprising a step of forming an insulating film that comprises Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), (La) lanthanum, Gd (gadolinium), Dy (dysprosium) and Nd (neodymium), between the substrate and the plurality of TFTs.

59. A method according to claim 52 further comprising a step of forming an insulating film that comprises Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), (La) lanthanum, Gd (gadolinium), Dy (dysprosium) and Nd (neodymium), between the substrate and the plurality of TFTs.